# 2.5V Drive Nch+Nch MOSFET **US6K1**

### Structure

Silicon N-channel MOSFET

### Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TUMT6).
- 3) Low voltage drive (2.5V drive).

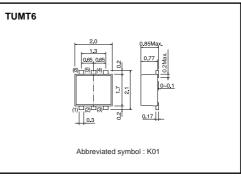
### Applications

Switching

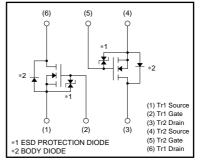
### Packaging specifications

	Package	Taping
Туре	Code	TR
	Basic ordering unit (pieces)	3000
US6K1		0

### •Dimensions (Unit : mm)



### Inner circuit



### •Absolute maximum ratings (Ta=25°C)

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Parameter		Symbol	Limits	Unit
Drain-source voltage		VDSS	30	V
Gate-source voltage		Vgss	12	V
Droin ourront	Continuous	ID	±1.5	А
Drain current	Pulsed	IDP <sup>*1</sup>	±6	А
Source current	Continuous	ls	0.6	A
(Body diode)	Pulsed	I <sub>SP</sub> *1	6	А
Total power dissipation		Pp *2	1.0	W / TOTAL
		гD	0.7	W / ELEMENT
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

\*1 Pw≤10μs, Duty cycle≤1% \*2 Mounted on a ceramic board

### Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	125	°C/W / TOTAL
	Run(cn-a)	179	°C/W / ELEMENT

\* Mounted on a ceramic board



# US6K1

## Transistors

### •Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	lgss	-	-	10	μA	Vgs=12V, Vds=0V	
Drain-source breakdown voltage	V(BR) DSS	30	-	-	V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V	
Zero gate voltage drain current	IDSS	-	-	1	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> =0V	
Gate threshold voltage	VGS (th)	0.5	-	1.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	
Static drain-source on-state resistance	RDS (on)*	-	170	240	mΩ	I <sub>D</sub> = 1.5A, V <sub>GS</sub> = 4.5V	
		-	180	250	mΩ	I <sub>D</sub> = 1.5A, V <sub>GS</sub> = 4.0V	
		-	240	340	mΩ	I <sub>D</sub> = 1.5A, V <sub>GS</sub> = 2.5V	
Forward transfer admittance	Y <sub>fs</sub> *	1.5	_	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1.5A	
Input capacitance	Ciss	-	80	_	pF	V <sub>DS</sub> = 10V	
Output capacitance	Coss	-	13	-	рF	V <sub>GS</sub> =0V	
Reverse transfer capacitance	Crss	-	12	-	рF	f=1MHz	
Turn-on delay time	td (on) *	-	7	_	ns	Vdd≒ 15V	
Rise time	tr *	-	9	_	ns	$I_{D}=0.75A$	
Turn-off delay time	td (off) *	-	15	_	ns	VGs= 4.5V R∟= 20Ω	
Fall time	t <sub>f</sub> *	-	6	_	ns	$R_G = 10\Omega$	
Total gate charge	Qg *	-	1.6	2.2	nC	V <sub>DD</sub> ≒15V	
Gate-source charge	Q <sub>gs</sub> *	-	0.5	-	nC	V <sub>GS</sub> = 4.5V	
Gate-drain charge	Q <sub>gd</sub> *	_	0.3	-	nC	I <sub>D</sub> = 1.5A	

### •Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd		-	1.2	V	Is= 0.6A, V <sub>GS</sub> =0V

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